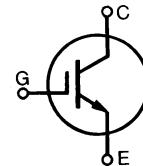


# HiPerFAST™ IGBT

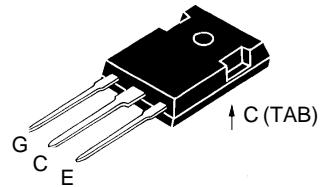
## IXGH32N60B

**$V_{CES}$**  = 600 V  
 **$I_{C25}$**  = 60 A  
 **$V_{CE(sat)}$**  = 2.5 V  
 **$t_{fi}$**  = 80 ns



Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	600	V
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GE} = 1 \text{ M}\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_c = 25^\circ\text{C}$	60	A
$I_{C90}$	$T_c = 90^\circ\text{C}$	32	A
$I_{CM}$	$T_c = 25^\circ\text{C}, 1 \text{ ms}$	120	A
<b>SSOA (RBSOA)</b>	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 33 \Omega$ Clamped inductive load, $L = 100 \mu\text{H}$	$I_{CM} = 64$ @ $0.8 V_{CES}$	A
$P_c$	$T_c = 25^\circ\text{C}$	200	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
$M_d$	Mounting torque (M3)	1.13/10 Nm/lb.in.	
<b>Weight</b>		TO-247 AD	6 g

TO-247 AD



G = Gate, C = Collector,  
E = Emitter, TAB = Collector

### Features

- International standard package JEDEC TO-247 AD
- High current handling capability
- Newest generation HDMOS™ process
- MOS Gate turn-on
  - drive simplicity

### Applications

- PFC circuits
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

### Advantages

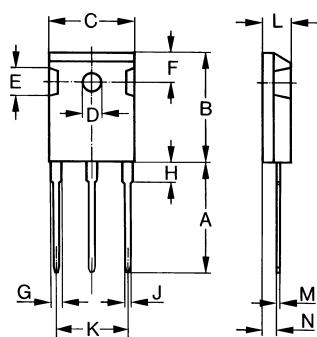
- High power density
- Very fast switching speeds for high frequency applications

Symbol	Test Conditions	Characteristic Values		
		( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	min.	typ.
$BV_{CES}$	$I_C = 250 \mu\text{A}, V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	2.5		V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	200	$\mu\text{A}$ 1 mA
$I_{GES}$	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$		$\pm 100$	nA
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15 \text{ V}$		2.5	V

Symbol	Test Conditions	Characteristic Values			
		( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	min.	typ.	max.
$g_{fs}$	$I_C = I_{C90}$ ; $V_{CE} = 10 \text{ V}$ , Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $\leq 2\%$	15	20	S	
$C_{ies}$	$V_{CE} = 25 \text{ V}$ , $V_{GE} = 0 \text{ V}$ , $f = 1 \text{ MHz}$	2500		pF	
		230		pF	
		70		pF	
$Q_g$	$I_C = I_{C90}$ , $V_{GE} = 15 \text{ V}$ , $V_{CE} = 0.5 V_{CES}$	125	150	nC	
		23	35	nC	
		50	75	nC	
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b>		25	ns	
	$I_C = I_{C90}$ , $V_{GE} = 15 \text{ V}$ , $L = 100 \mu\text{H}$ ,		30	ns	
	$V_{CE} = 0.8 V_{CES}$ , $R_G = R_{off} = 4.7 \Omega$		100	200	ns
	Remarks: Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 \cdot V_{CES}$ ,		80	150	ns
	higher $T_J$ or increased $R_G$		0.8	1.6	mJ
	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b>		25	ns	
$t_{ri}$	$I_C = I_{C90}$ , $V_{GE} = 15 \text{ V}$ , $L = 100 \mu\text{H}$		35	ns	
	$V_{CE} = 0.8 V_{CES}$ , $R_G = R_{off} = 4.7 \Omega$		0.3	mJ	
	Remarks: Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 \cdot V_{CES}$ ,		120	ns	
	higher $T_J$ or increased $R_G$		120	ns	
			1.4	mJ	
$R_{thJC}$				0.62	K/W
$R_{thCK}$			0.25		K/W

IXGH 32N60B characteristic curves are located in the IXGH 32N60BU1 data sheet.

#### TO-247 AD (IXGH) Outline



Dim.	Millimeter Min. Max.	Inches Min. Max.
A	19.81 20.32	0.780 0.800
B	20.80 21.46	0.819 0.845
C	15.75 16.26	0.610 0.640
D	3.55 3.65	0.140 0.144
E	4.32 5.49	0.170 0.216
F	5.4 6.2	0.212 0.244
G	1.65 2.13	0.065 0.084
H	- 4.5	- 0.177
J	1.0 1.4	0.040 0.055
K	10.8 11.0	0.426 0.433
L	4.7 5.3	0.185 0.209
M	0.4 0.8	0.016 0.031
N	1.5 2.49	0.087 0.102